Q1

(a): mismatch of the input transistors and components during fabrication of the silicon die and stresses placed on the die during the packaging process

(b):

$$V = -\int \frac{V_{\rm os}}{RC} dt$$

$$\begin{aligned} \bullet \ V_{\text{out}} &= R_2 I_{B(-)} - I_{B(+)} R_P \Big(1 + \frac{R_2}{R_1} \Big) \\ \bullet \ R_P &= \frac{R_1 R_2}{R_1 + R_2} \end{aligned}$$

•
$$R_P = \frac{R_1 R_2}{R_1 + R_2}$$

- $\mathrm{CMRR} = \frac{A_{\mathrm{dm}}}{A_{\mathrm{cm}}}$ In high-precision circuits, such as instrumentation amplifiers, even small common-mode voltages can lead to significant output errors when the CMRR is finite.

•
$$V_{\rm out} = 105 \ {\rm nA} \times 10^6 = 105 \ {\rm mV}$$

•
$$R_3 = R_1 \parallel R_2 = 9901\Omega$$

• -45.096 mV

(f)? 滤除电源噪声

$\mathbf{Q}\mathbf{2}$

$$v_o = v_{\mathrm{in}(\text{--})} - v_{\mathrm{in}(\text{+-})}$$

(b)

(c)

$$v_{\rm out} = v_{\rm in(-)} - v_{\rm in(+)} + v_{\rm os} + I_{\rm os} R$$

$$\mathrm{RTO} = v_{\mathrm{os}} + I_{\mathrm{os}} R; R = 10 k \Omega$$

(d)

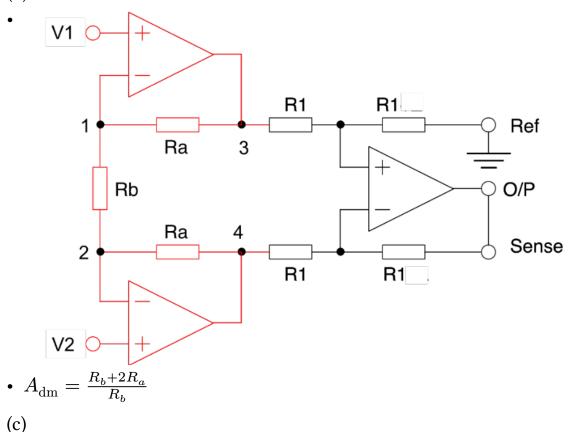
$$F = V_{os} + I_{os}R$$

Q3

(a)

To achieve a high CMRR.

(b)



Twisted pair advantage: Common mode noise.

- The idea of a twisted pair cable is that the currents induced in each of the two wires are very nearly equal.
 - The twisting ensures that the two wires are on average the same distance from the interfering source and are, therefore, affected equally.
 - The "noise" then produces a common-mode signal which can be cancelled due to the very high CMRR of the differential amplifier.
 - This helps ensure that only the wanted difference signal is processed.
- 高輸入阻抗:确保从源设备(如传感器)获取信号时不会对其造成负载影响。
- 高 CMRR:能够有效抑制与信号无关的共模干扰,如电源线噪声和环境干扰。

• 可调增益:可以通过外部电阻简单调整增益,以适应不同的测量需求。

Q4

(a)

Summarize possible strategies for improving the Signal to Noise ratio (SNR) when using operational amplifiers:

- 1. Select a Low-Noise Op-Amp:减少输入的电流与电压噪声
- 2. Optimize Gain Settings(增加信号增益,抑制噪声增益)
- 3. Optimize Gain Settings(减少电阻所产生的热噪声)
- 4. Minimize Bandwidth(在输出端添加一个滤波器)
- 5. Shielding(屏蔽, 比如用双绞线)

(b):

见 App.typ (c)

• NEB =
$$n \times \frac{\text{GBW}}{\text{Noise Gain}} = 1.57 \times \frac{5.2 \text{MHz}}{101} = 80.8 \text{ kHz thermal:} 1.159 \times 10^{-5} \text{ and } 1.159 \times 10^{-6}$$

$$\begin{split} \bullet \ E_{\text{opamp}} &= e_{\text{nw}} \cdot \sqrt{\text{NEB}} = 4.55 \times 10^{-6} \\ R_3 &= R_1 \parallel R_2 = 1 k \Omega \\ E_{R_1} &= G_n \cdot 1.16 \times 10^{-6} = 117.16 \mu V \\ E_{R_2} &= G_n \cdot 1.16 \times 10^{-5} = 1170.59 \mu V \\ E_{\text{opamp}} &= G_n \cdot 4.55 \mu V = 459.55 \mu V \\ E_{R_3} &= G_n \cdot 1.15 \mu V = 116.15 \mu V \\ E_{\text{tot}} &= \sqrt{117.16^2 + 1170.59^2 + 116.15^2 + 459.55^2} = 1.262 \text{ mV} \\ V_{\text{sig}} &= \frac{2}{\sqrt{2}} = 1.414 V \\ \text{SNR} &= 20 \log_{10} \left(\frac{1.414}{1.262 \text{ mV}} \right) = 60.98 \text{ dB} \end{split}$$